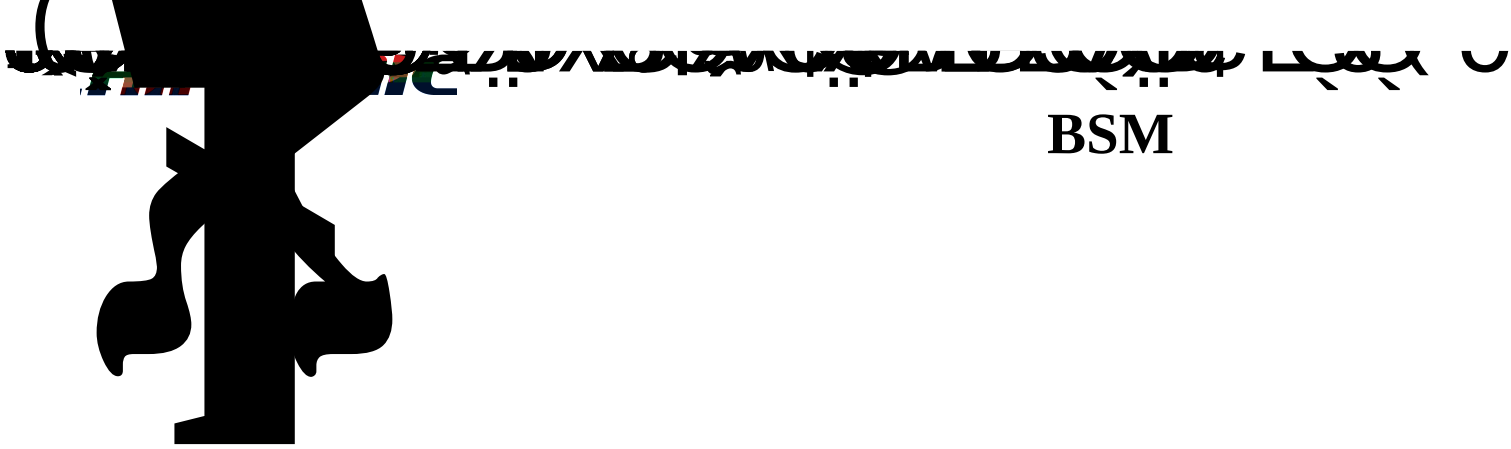
BSM4005H4C [illegible] 40V H N [illegible] MOSFET

[illegible]

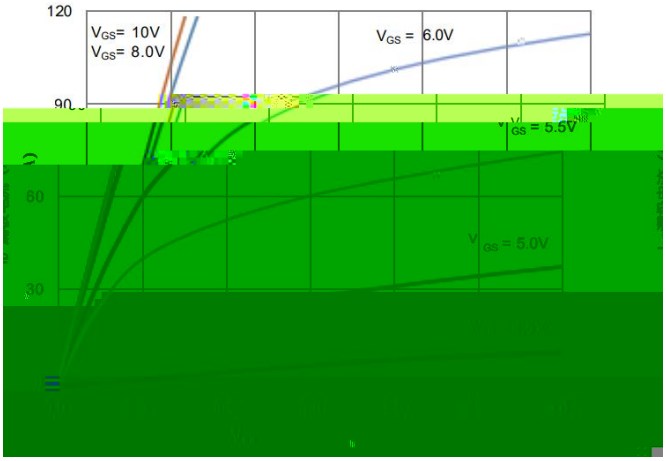
V_{DS}	$R_{DS\ on}$ [illegible] _MAX	I_{D_MAX}
40 V	4mΩ @V_{GS} = 10V	45 A

[illegible]

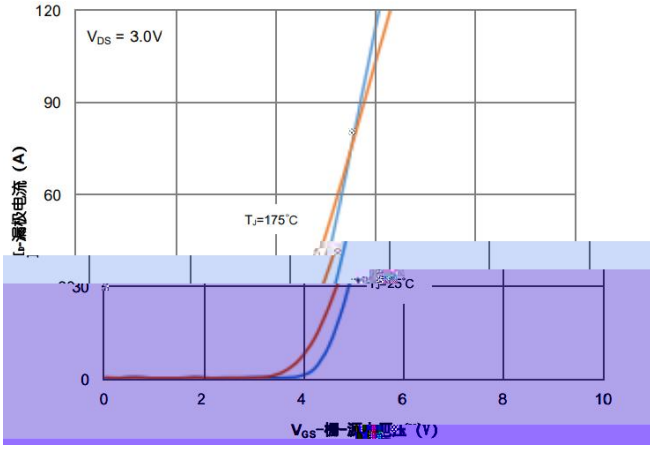
	(6)					
		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	40		V
		I_{DSS}	V_{DS} = 40V, V_{GS} = 0V		1.0	μA
			T_J = 125°C		100	μA
		I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V		±100	μA
	(6)					
		$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250μA	2.0	3.0	4.0	V
-		$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		4.0	4.7	mΩ



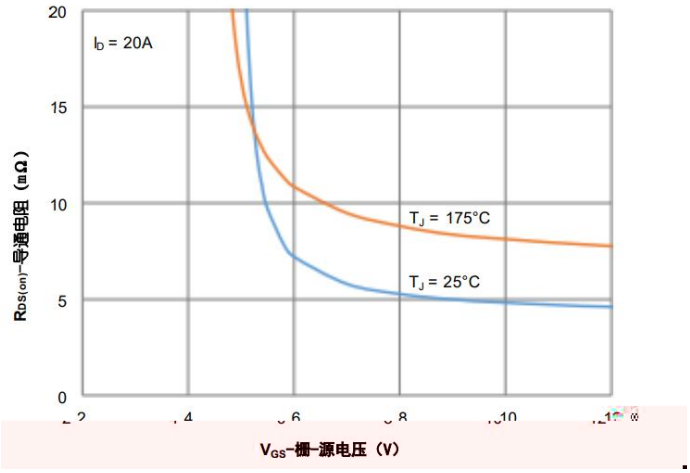
BSM


120
90
60
30
V_{GS}= 10V
V_{GS}= 8.0V
V_{GS} = 6.0V
V_{GS} = 5.5V
V_{GS} = 5.0V

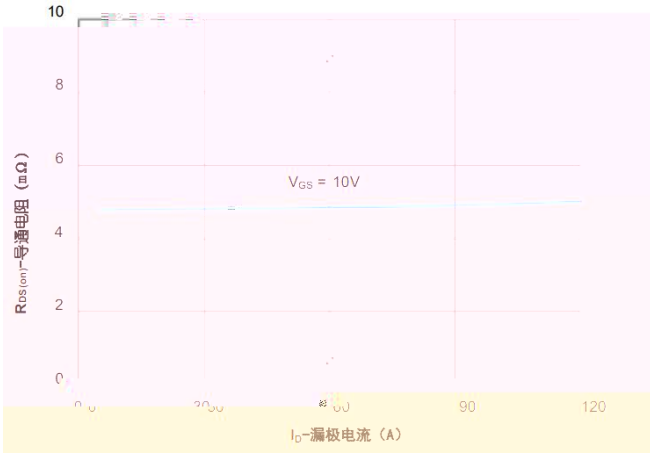
1


120
90
60
30
0
V_{DS} = 3.0V
T_J=175°C
T_J=25°C
0
2
4
6
8
10
V_{GS}-栅-源电压（V）

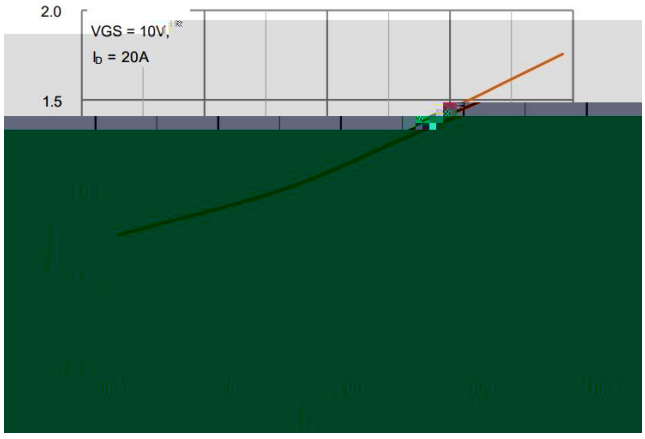
2


20
15
10
5
0
I_D = 20A
T_J = 175°C
T_J = 25°C
$R_{DS(on)}$-导通电阻（mΩ）
V_{GS}-栅-源电压（V）

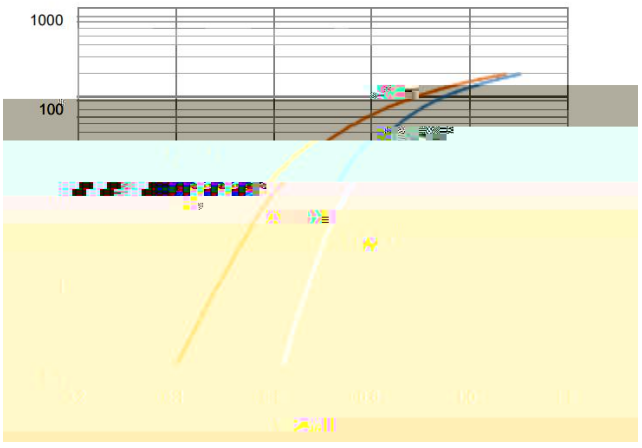
3


10
8
6
4
2
0
V_{GS} = 10V
$R_{DS(on)}$-导通电阻（mΩ）
90
120
I_D-漏极电流（A）

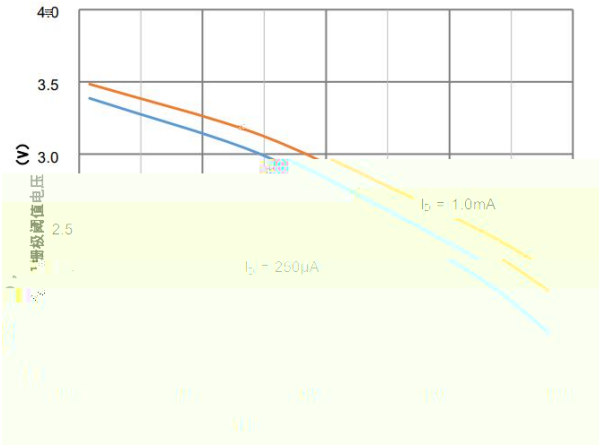
4


2.0
1.5
VGS = 10V
I_D = 20A

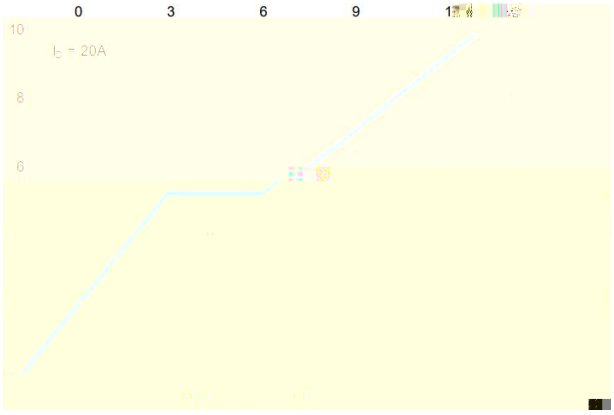
5


1000
100

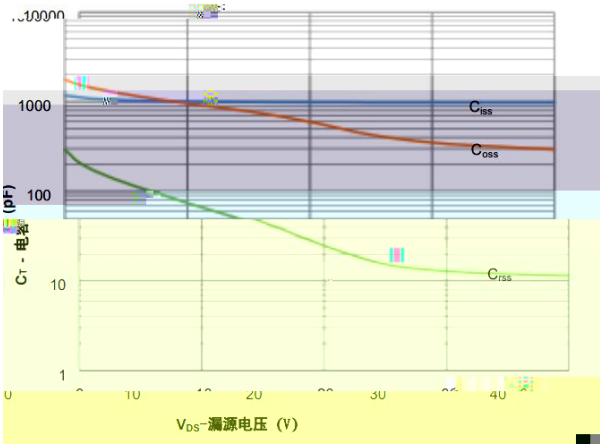
6


4.0
3.5
3.0
2.5
(V)
I_D = 1.0mA
I_D = 250μA

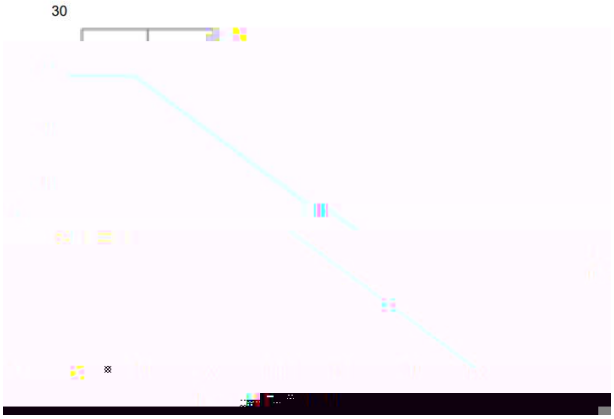
7


0
3
6
9
10
8
6
I_D = 20A

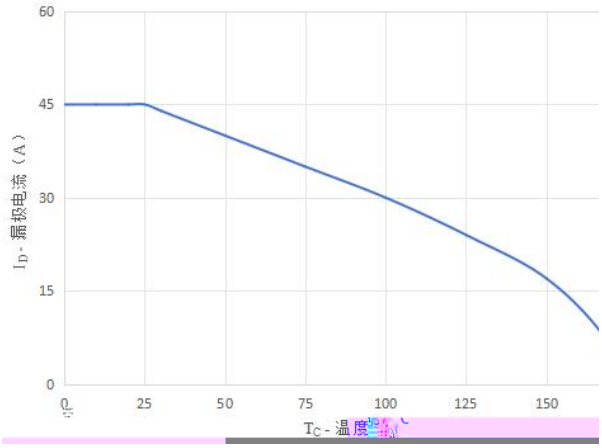
8


10000
1000
100
10
1
(pF)
C_{iss}
C_{oss}
C_{rss}
0
10
20
30
40
V_{DS}-漏源电压（V）

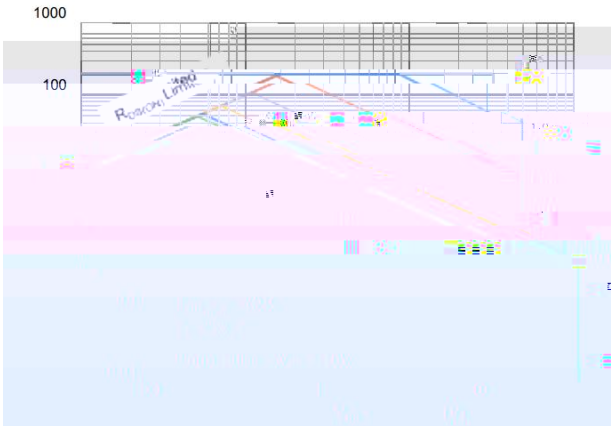
9


30

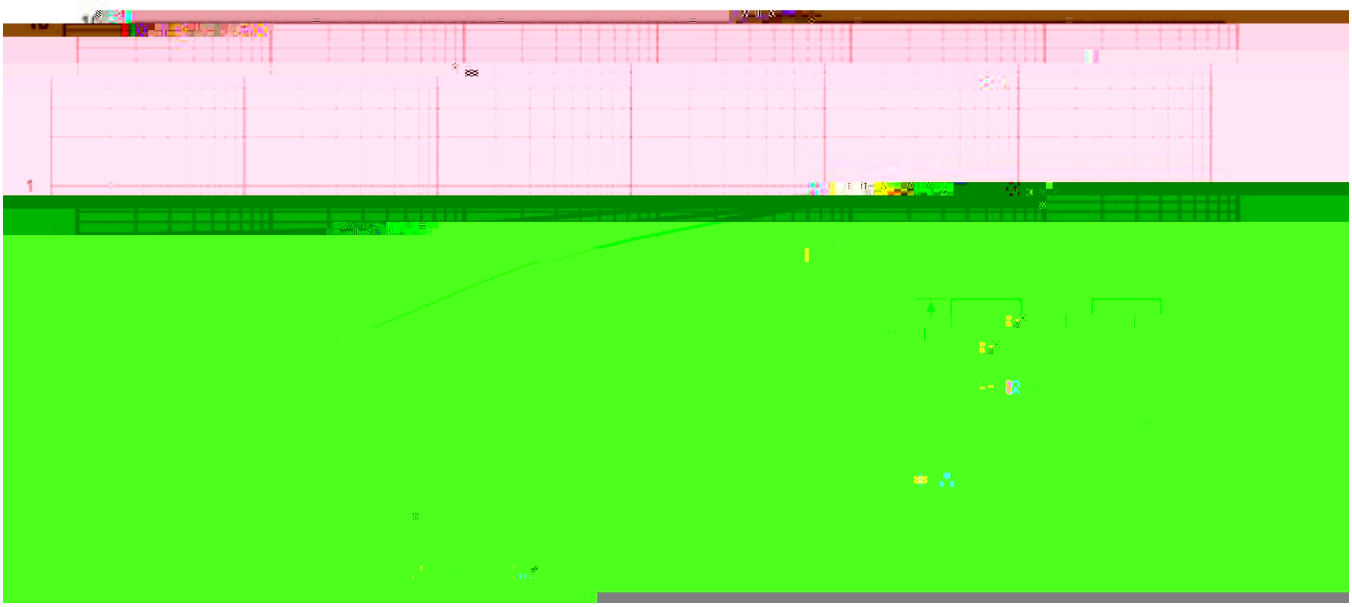
10


60
45
30
15
0
I_D - 漏极电流（A）
0
25
50
75
100
125
150
T_C - 温度

11

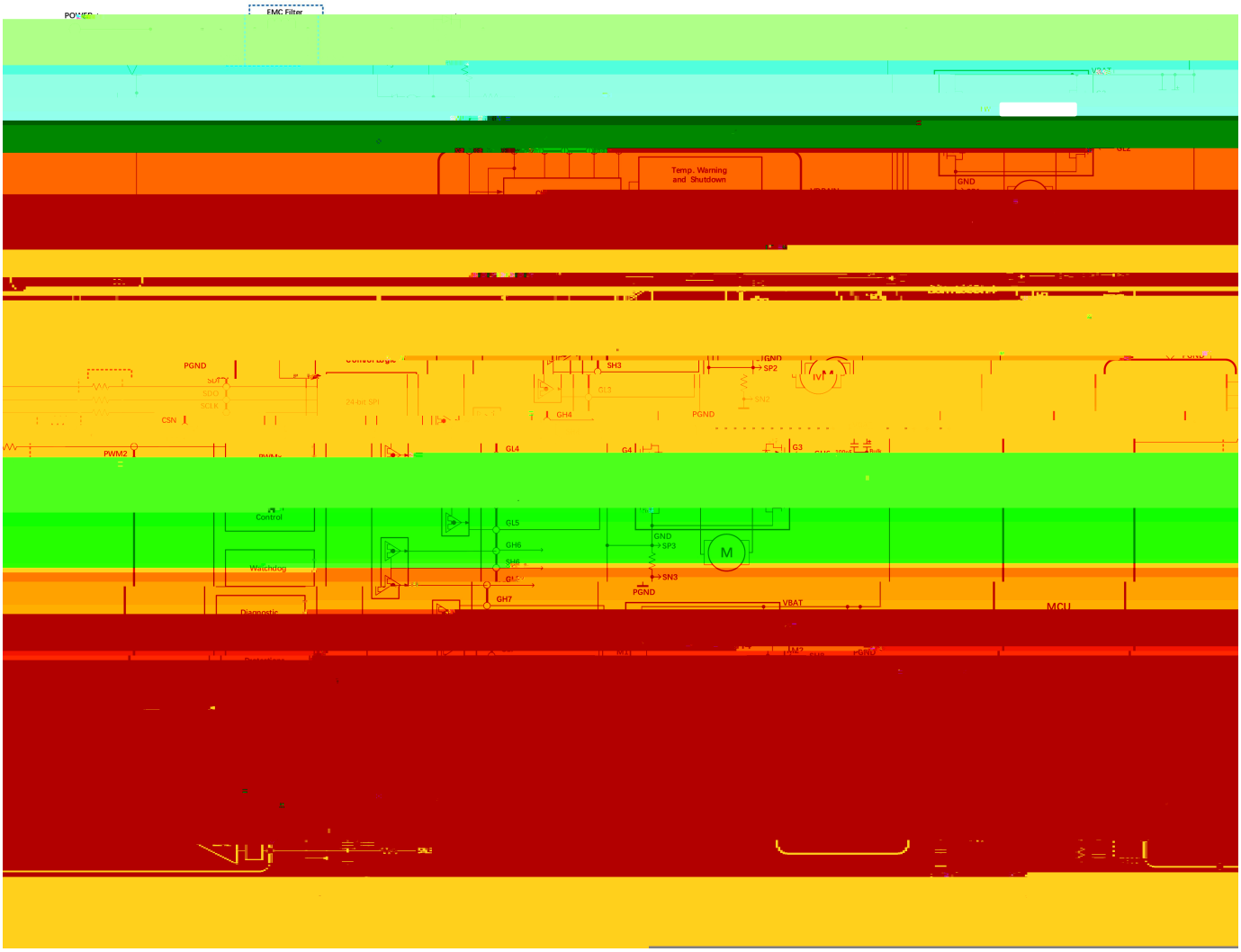

1000
100

12



13

Й ɻ ˜ ﻡﺨ



14

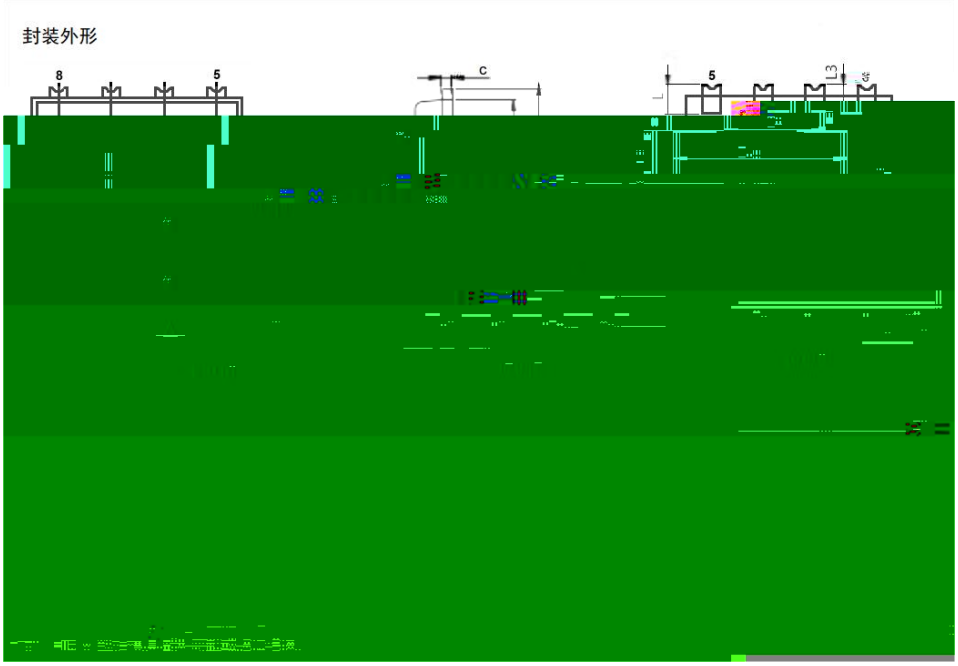
Note

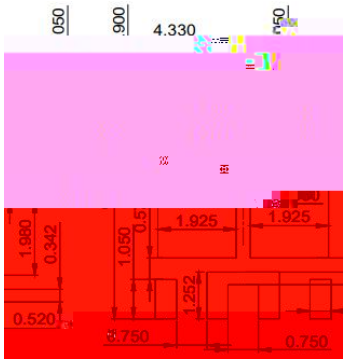
PGND

GND BSM4005H4C GND

SP3 SN3 SP4 SN3

封装外形





DIM.	MILLIMETER		
	MIN.	NOM.	MAX
			0.34
D	5.05	5.20	5.40
D1	4.95	5.05	5.15
D2	4.00	4.10	4.20
D3	1.73	1.83	1.93
D4	2.24	2.34	2.44
E	6.30	6.40	6.50
E1	5.75	5.8[illegible]	